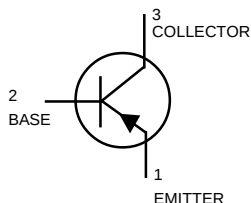


General Purpose Transistors

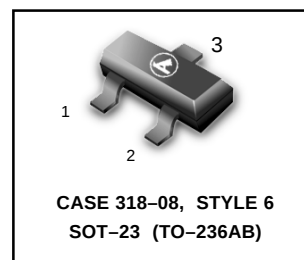
PNP Silicon



BCW29LT1
BCW30LT1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–32	Vdc
Collector–Base Voltage	V_{CBO}	–32	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current — Continuous	I_C	–100	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

DEVICE MARKING

BCW29LT1 = C1; BCW30LT1 = C2

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = -2.0\text{mAdc}$, $I_E = 0$)	$V_{(BR)CEO}$	–32	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -100\text{ }\mu\text{Adc}$, $V_{EB} = 0$)	$V_{(BR)CES}$	–32	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)CBO}$	–32	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	–5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = -32\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	–100	nAdc
($V_{CB} = -32\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)		—	–10	μAdc

1. FR–5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

BCW29LT1 BCW30LT1
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

ON CHARACTERISTICS

DC Current Gain ($I_C = -2.0\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$)	BCW29 BCW30	h_{FE}	120 215	260 500	— —
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mAdc}$, $I_B = -0.5\text{ mAdc}$)		$V_{CE(sat)}$	—	– 0.3	Vdc
Base–Emitter On Voltage ($I_C = -2.0\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$)		$V_{BE(on)}$	– 0.6	–0.75	Vdc

SMALL–SIGNAL CHARACTERISTICS

Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	7.0	pF
Noise Figure ($I_C = -0.2\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	—	10	dB

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TYPICAL NOISE CHARACTERISTICS

($V_{CE} = -5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

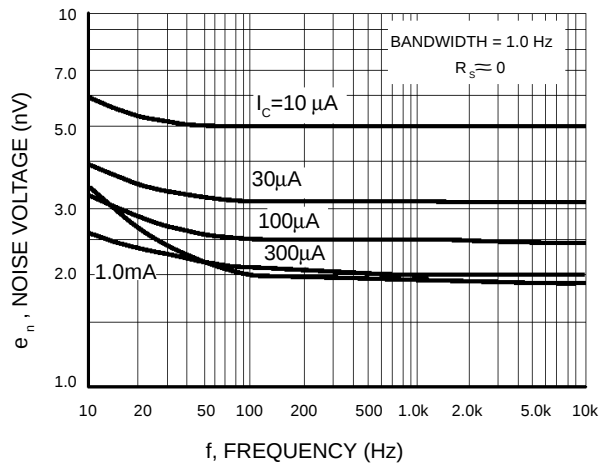


Figure 1. Noise Voltage

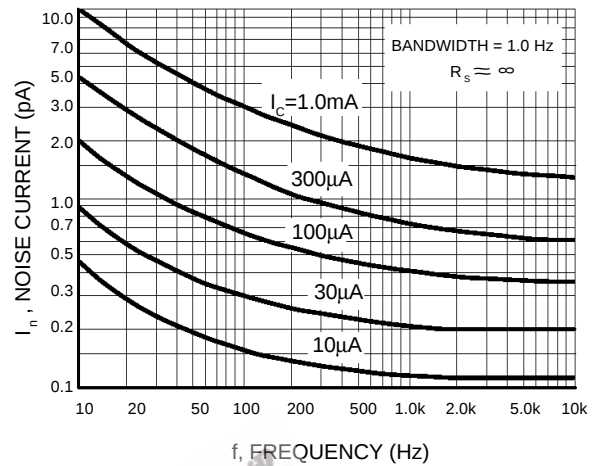


Figure 2. Noise Current

NOISE FIGURE CONTOURS

($V_{CE} = -5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

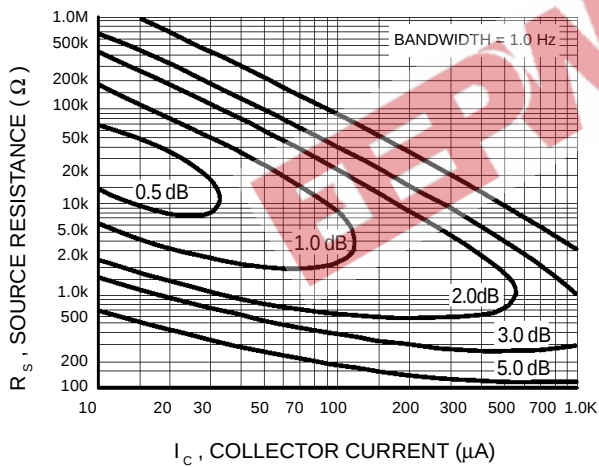


Figure 3. Narrow Band, 100 Hz

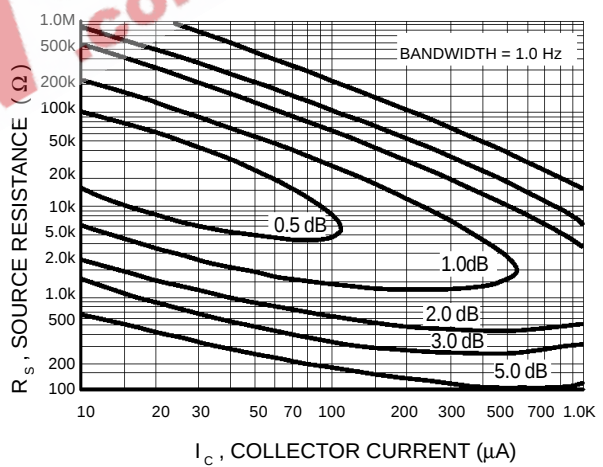


Figure 4. Narrow Band, 1.0 kHz

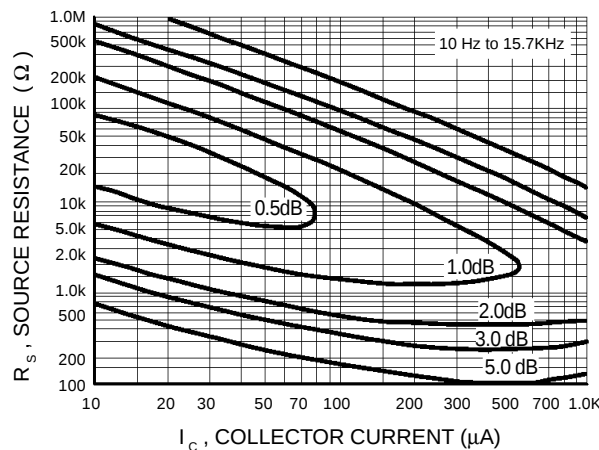


Figure 5. Wideband

Noise Figure is Defined as:

$$NF = 20 \log_{10} \left(\frac{e_n^2 + 4KTR_s + I_n^2 R_s^2}{4KTR_s} \right)^{1/2}$$

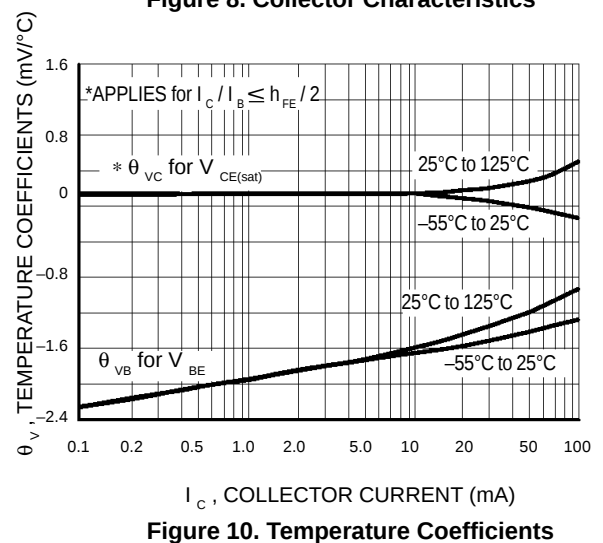
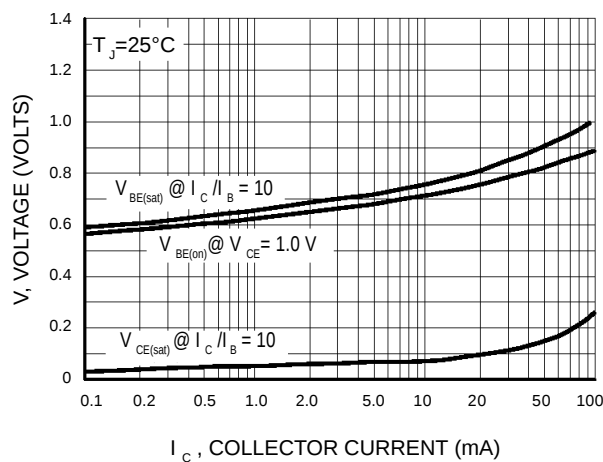
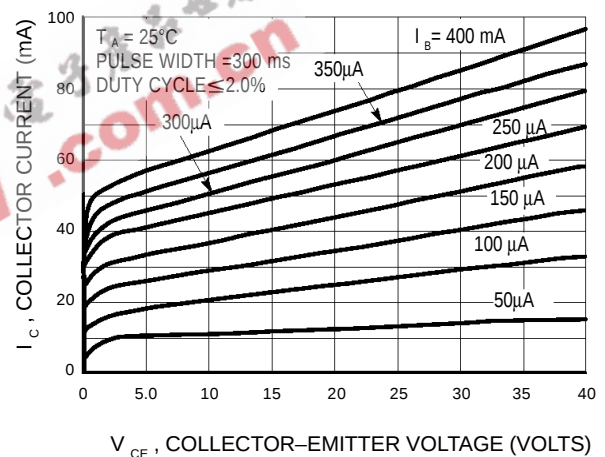
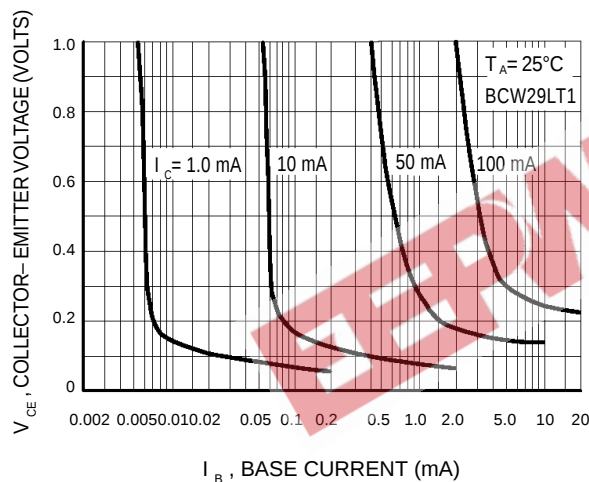
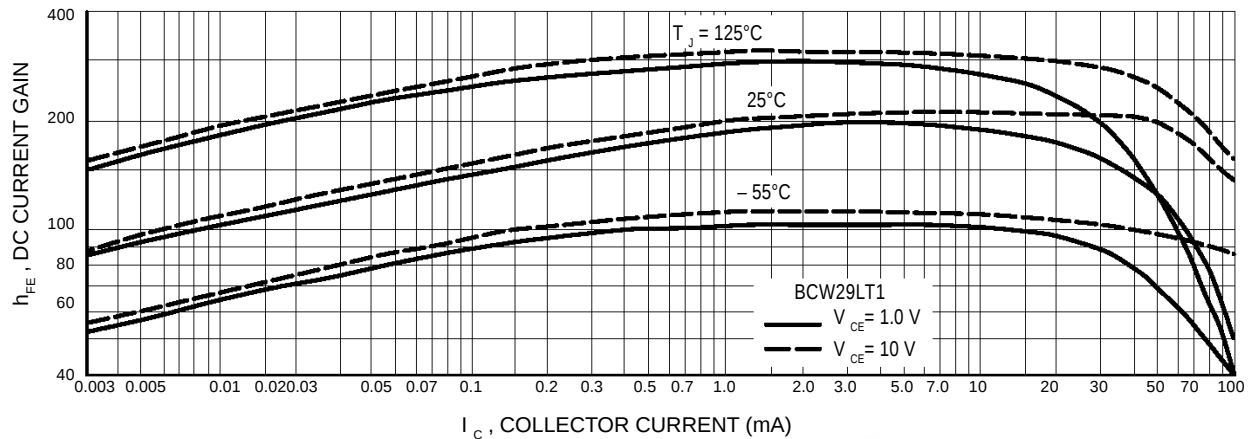
e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

I_n = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant ($1.38 \times 10^{-23} \text{ J/}^\circ\text{K}$)

T = Temperature of the Source Resistance ($^\circ\text{K}$)

R_s = Source Resistance (Ω)

BCW29LT1 BCW30LT1
TYPICAL STATIC CHARACTERISTICS


BCW29LT1 BCW30LT1

TYPICAL DYNAMIC CHARACTERISTICS

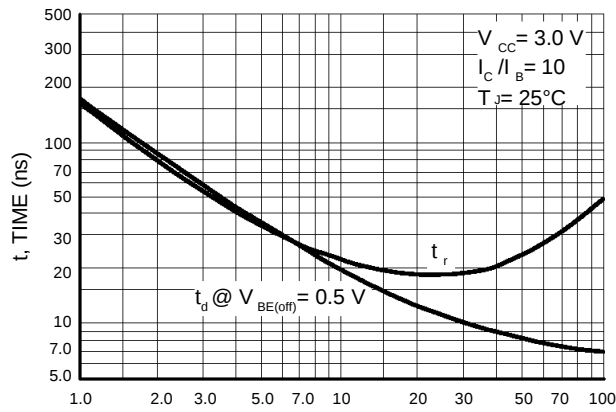


Figure 11. Turn-On Time

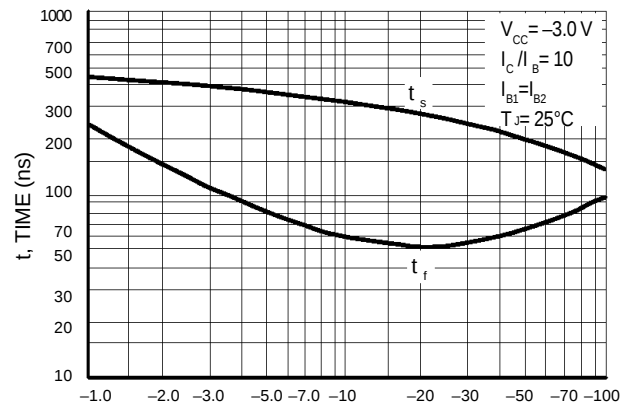


Figure 12. Turn-Off Time

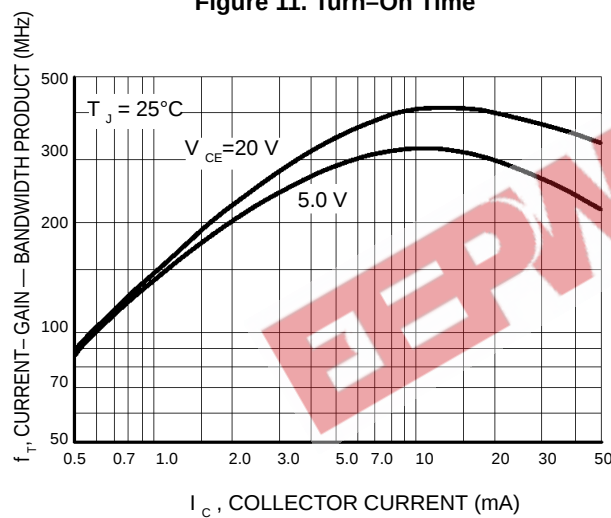


Figure 13. Current-Gain — Bandwidth Product

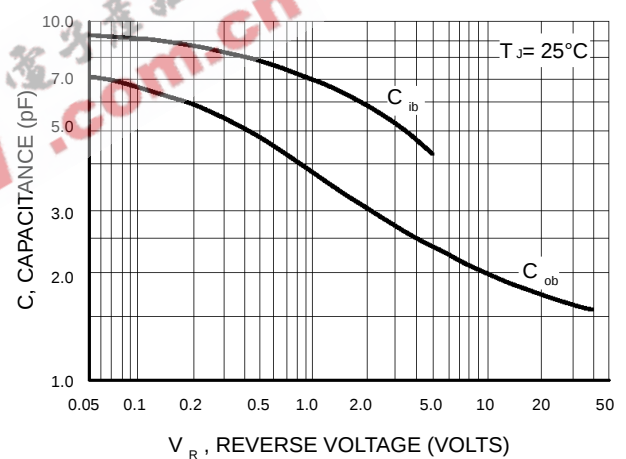


Figure 14. Capacitance

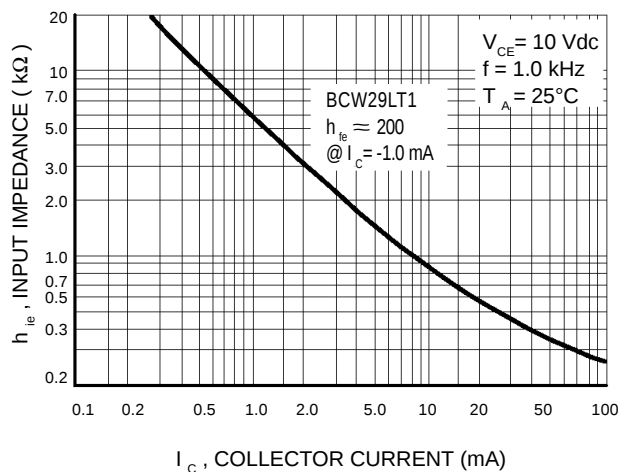


Figure 17. Input Impedance

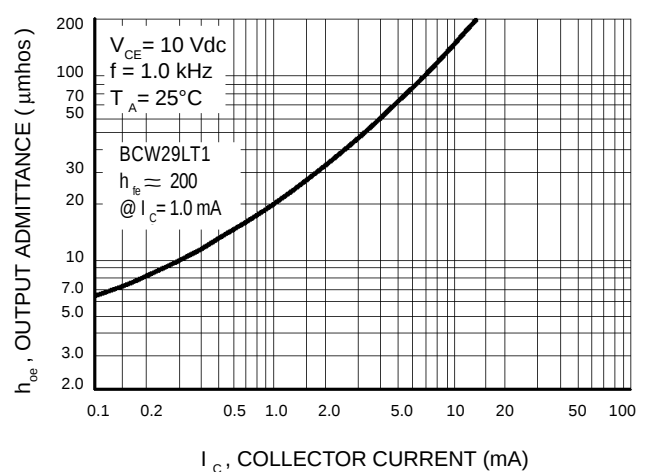
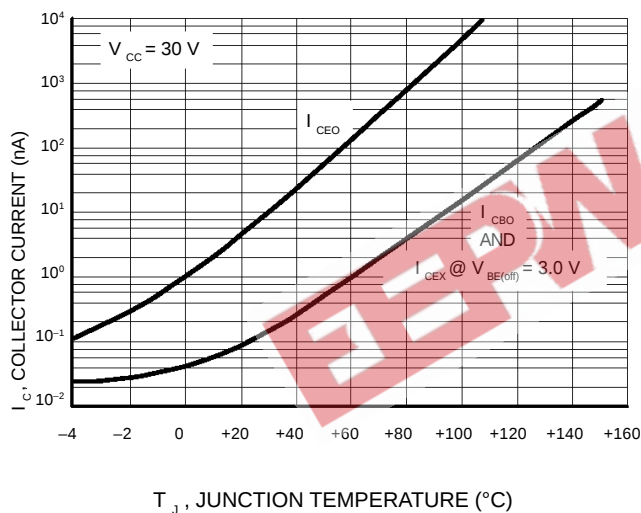
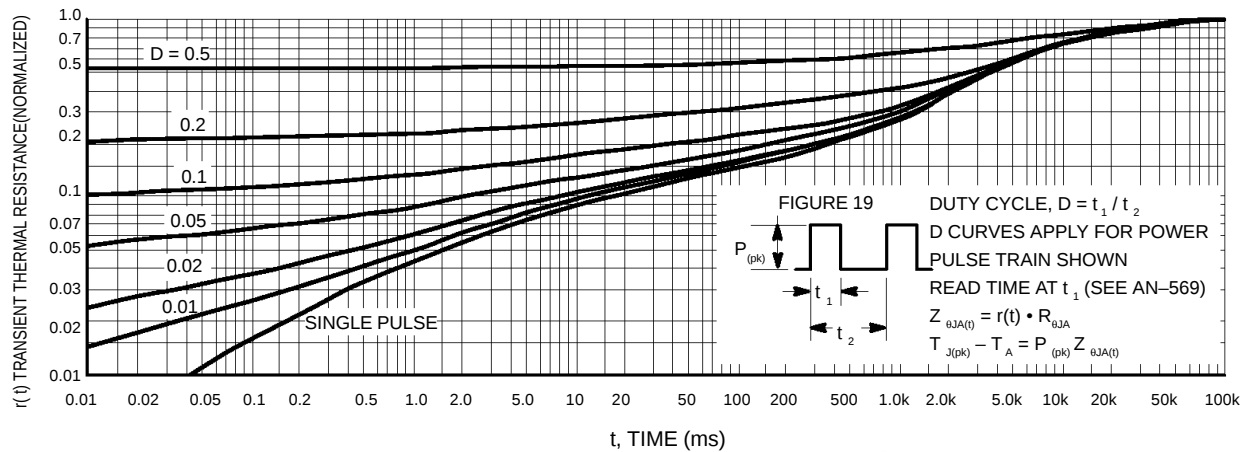


Figure 18. Output Admittance

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DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 17 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 17 by the steady state value $R_{\theta JA}$.

Example:

The BCW29LT1 is dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0$ ms, $t_2 = 5.0$ ms. ($D = 0.2$)

Using Figure 17 at a pulse width of 1.0 ms and $D = 0.2$, the reading of $r(t)$ is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see AN-569.